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Innovative Silicon's Pierre Fazan to Address Nano-Technology at Public Conference in Geneva

Z-RAM company's Founder and CTO joins celebrated panel to de-mystify the nano-scale electronics world

NANO TECHNOLOGIES SYMPOSIUM, Geneva, Switzerland — November 3, 2008 —

Pierre Fazan, Founder & CTO of Innovative Silicon, Inc. (ISi), the developer of the Z-RAM® zero-capacitor floating body memory technology, will today address a symposium on nano-technology, organized by the Swiss Utility Company, SIG, for their employees, customers and the Geneva Community.

The panel for the one-day event will include Professor P. Hoffmann from the École Polytechnique Fédérale de Lausanne (EPFL) billed as a famous scientist, the "charismatic adventurer" Bertrand Piccard, philosopher Pascal Boulanger, and Fazan who fulfils the role of passionate entrepreneur. All speakers will discuss the theme: "Nano-technologies – opportunities or risks?"

Fazan will present a definition of nano technology and nano dimensions, drawing on examples in nature and looking at products and applications of nano technology that are in general use today. He will continue by considering the semiconductor field, asking questions such as: "What is a chip?" and "What is a transistor – what do they look like?" Fazan will also look at the issue of transistor scaling – which is threatening to stall further miniaturization of the DRAM - then describe Innovative Silicon's Z-RAM memory.

About Innovative Silicon

Innovative Silicon, Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world's lowest-cost



semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World Economic Forum’s selection of ISi as a 2008 Technology Pioneer, and IEEE Spectrum Magazine’s selection of Z-RAM as the 2007 “Emerging Technology Most Likely to Succeed.” Z-RAM is a “Zero Capacitor,” true single-transistor floating body memory that eliminates the complex capacitor found in today’s DRAM technologies – a fundamental roadblock to Moore’s Law of scaling. Z-RAM provides semiconductor manufacturers a solution for nanoscale manufacturing processes that can dramatically lower semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling \$47 million, received over 30 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D, engineering and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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